

FIG.1

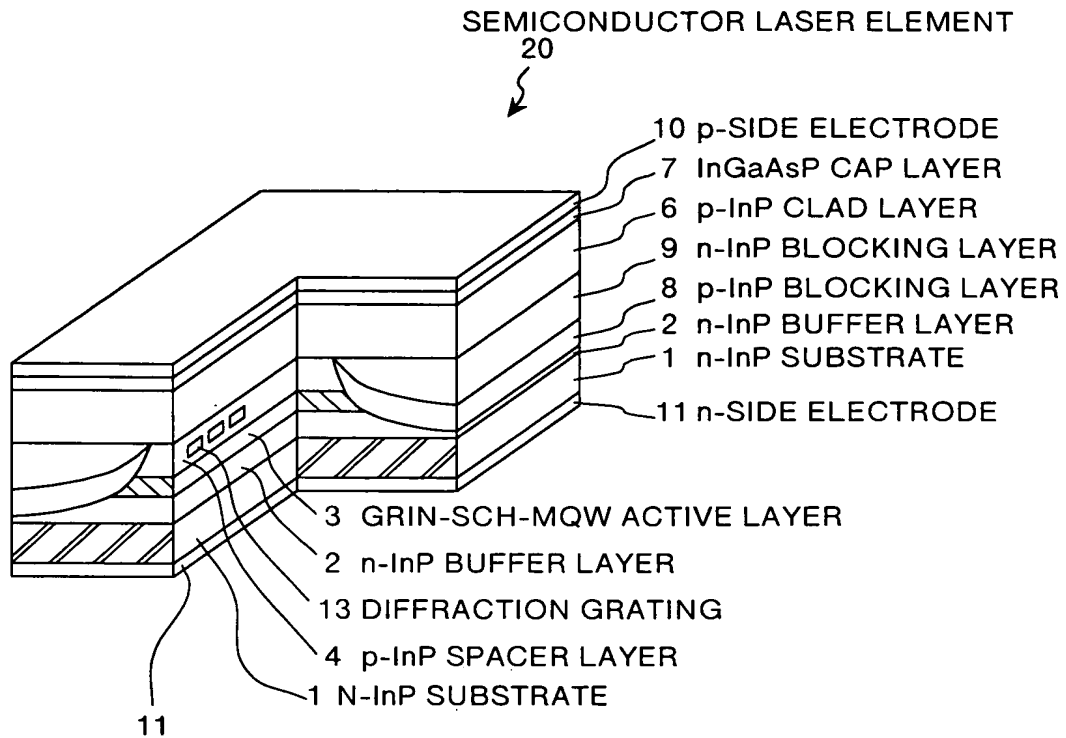


FIG.2

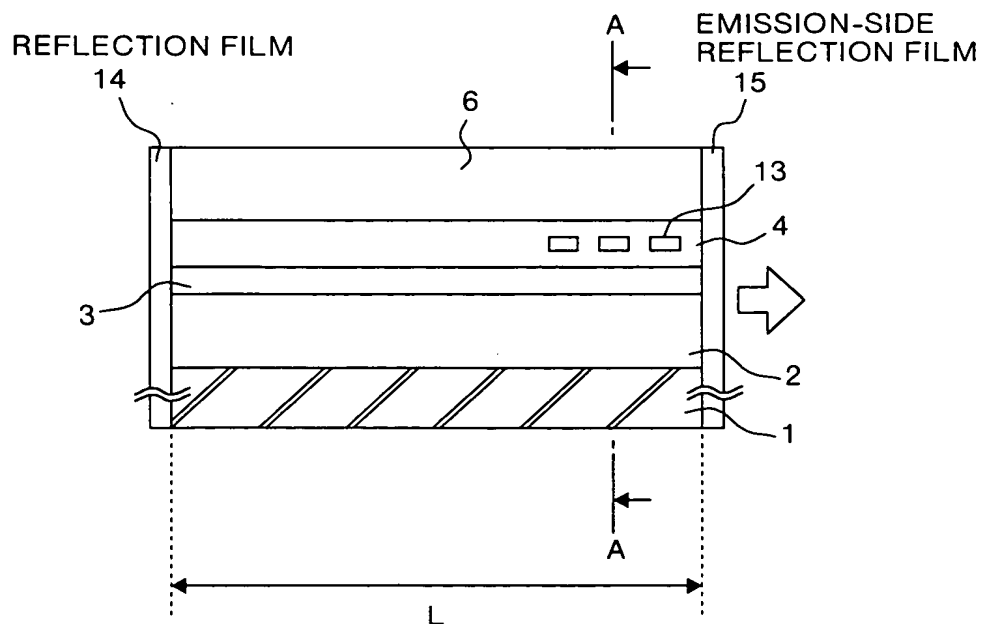


FIG.3

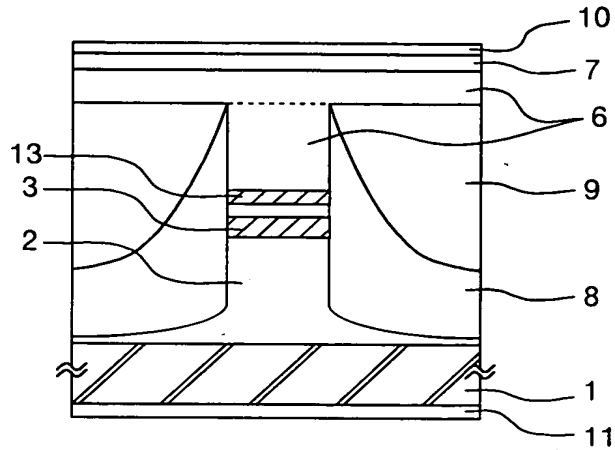
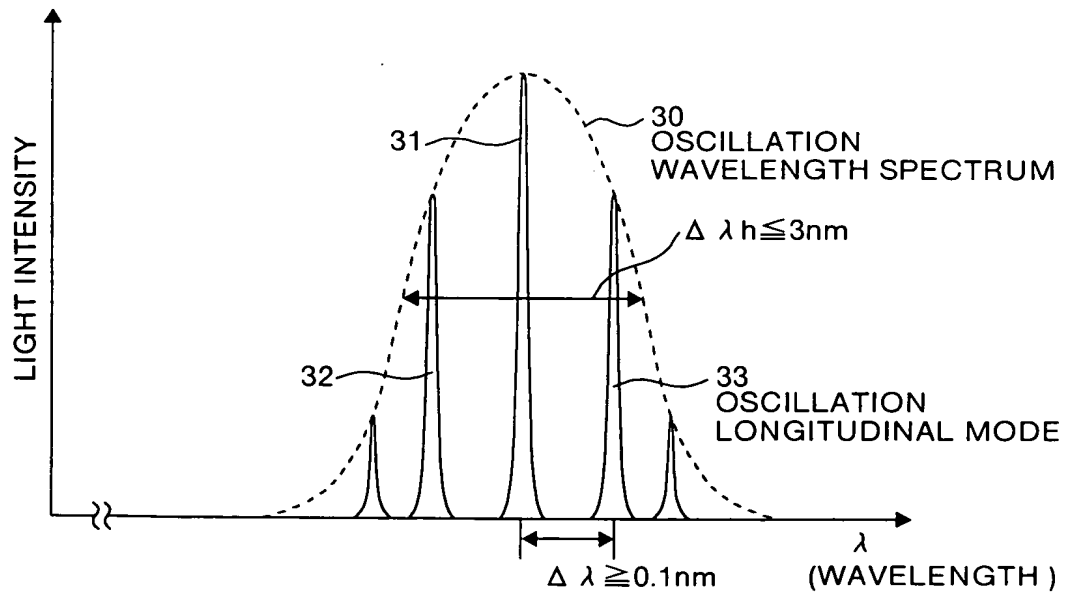


FIG.4



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FIG.5A

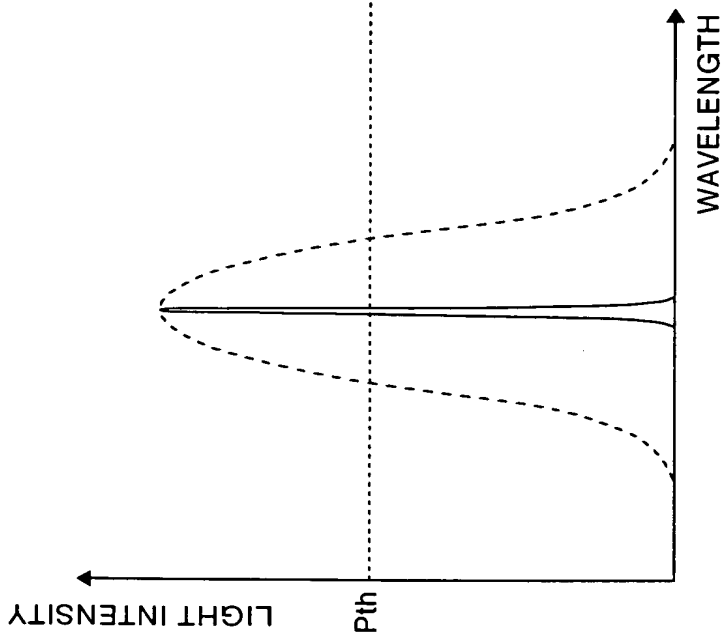
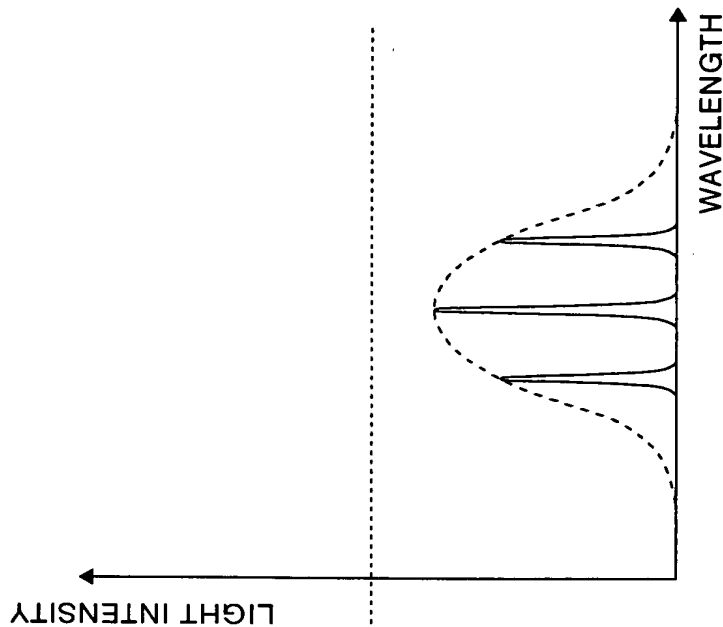
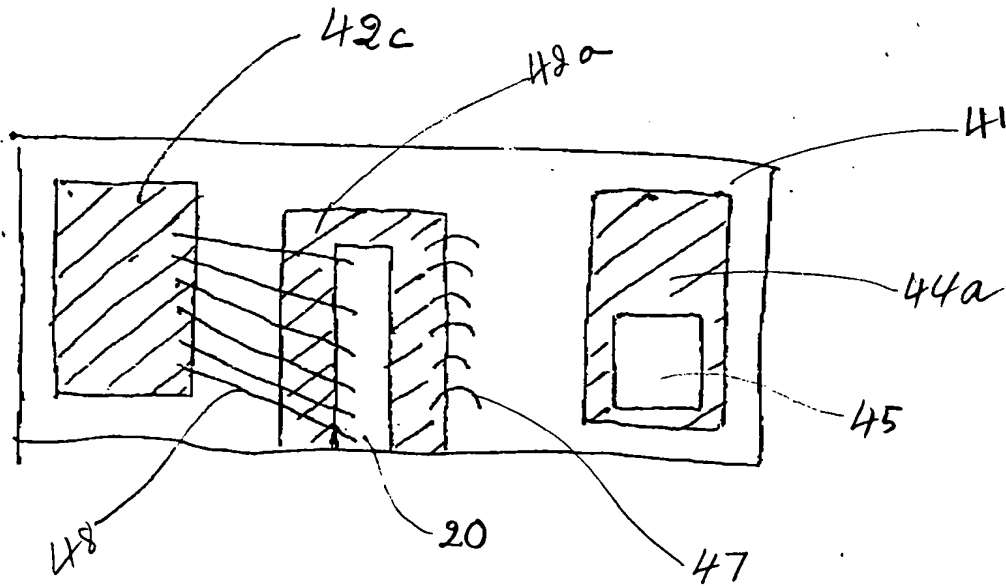


FIG.5B



The diagram illustrates a temperature control system for a semiconductor device. The device structure includes a substrate 41 with various layers and components: 42, 44, 42d, 42b, 44b, 45, 44a, 47, 42a, 48, and 49c. A current source 200 is connected to the device through a current detector 201. The current detector 201 sends a signal to a temperature control section 202, which is connected to a storage section 203. The temperature control section 202 is also connected to the device. A double-headed arrow indicates a relationship between the device and the temperature control section.

FIG. 6B



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FIG.7A

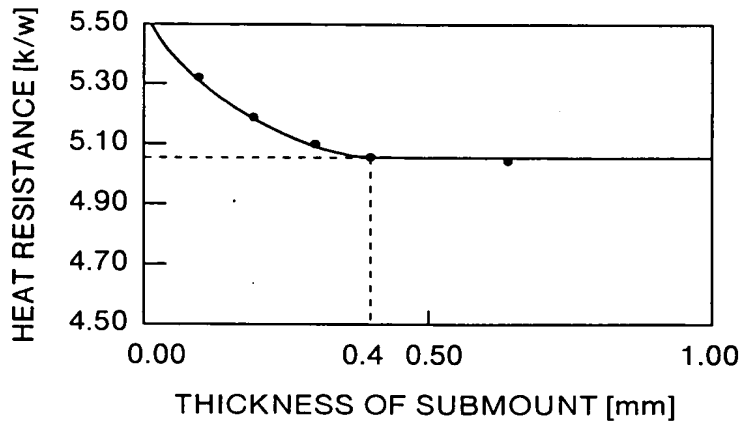


FIG.7B

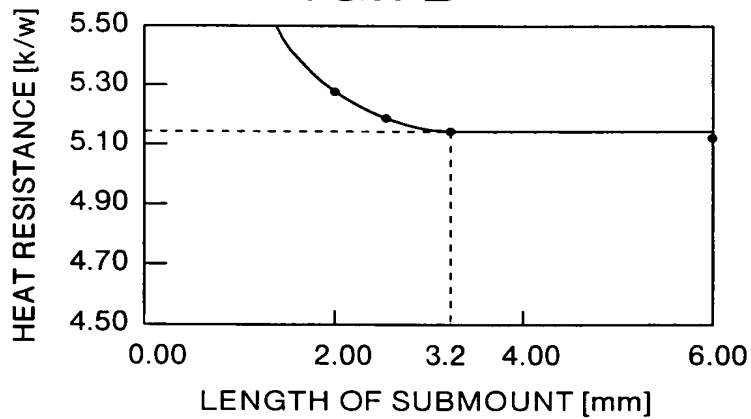
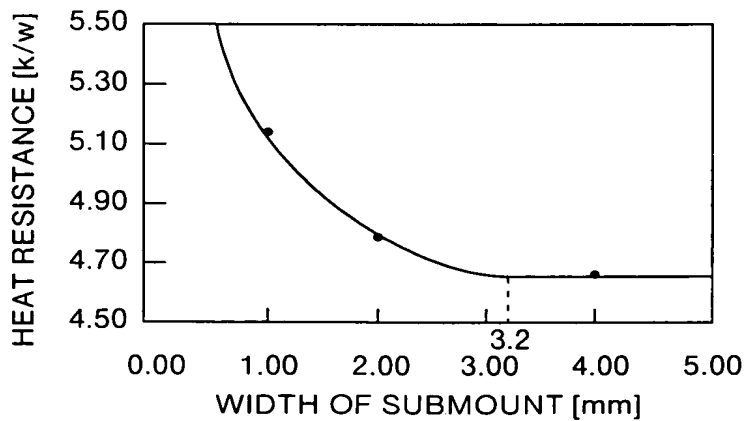
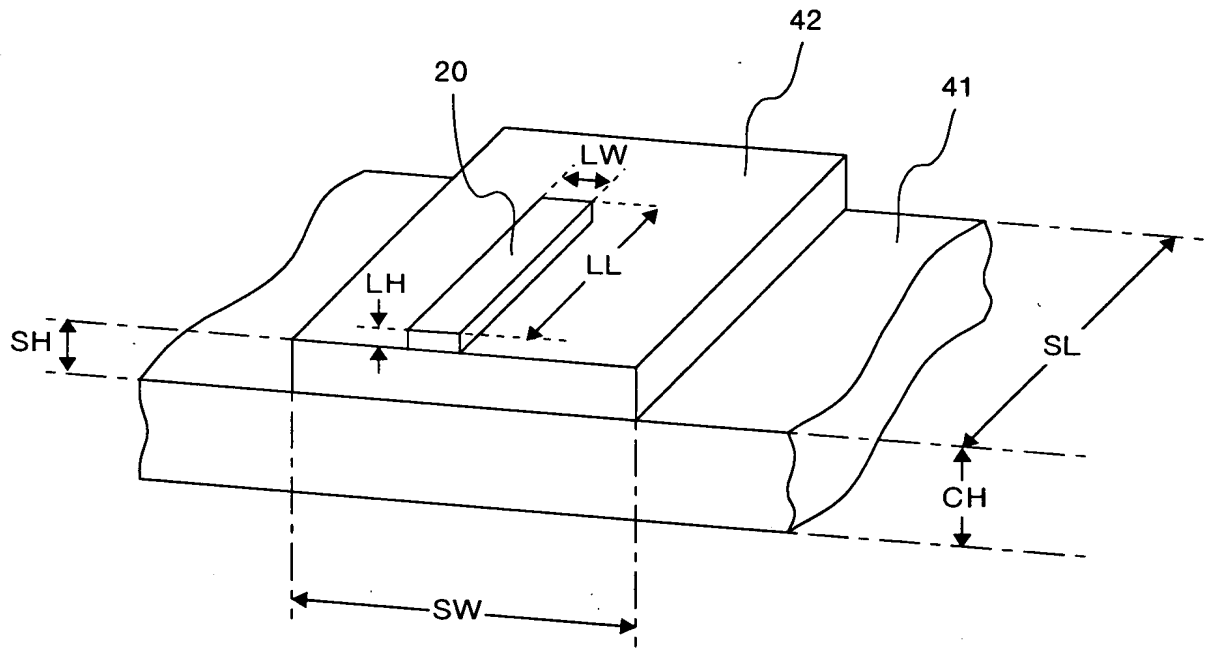


FIG.7C



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FIG.8



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FIG.9A

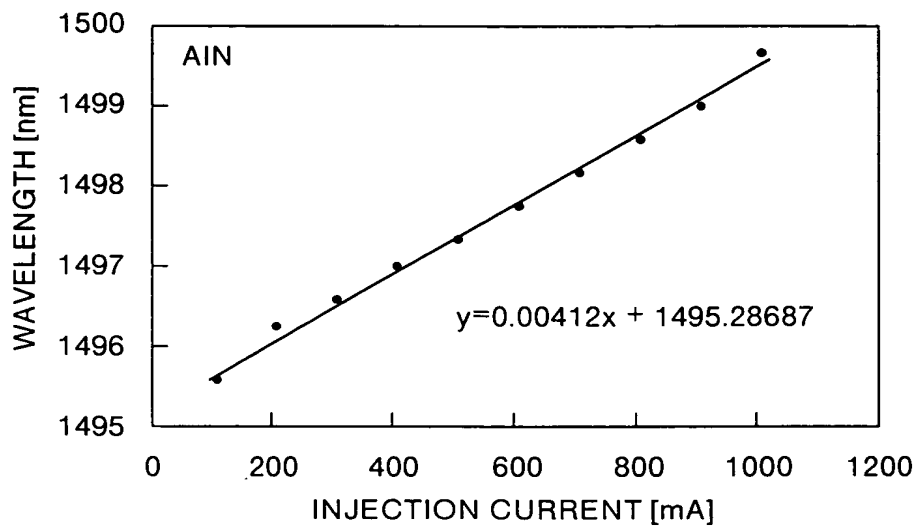


FIG.9B

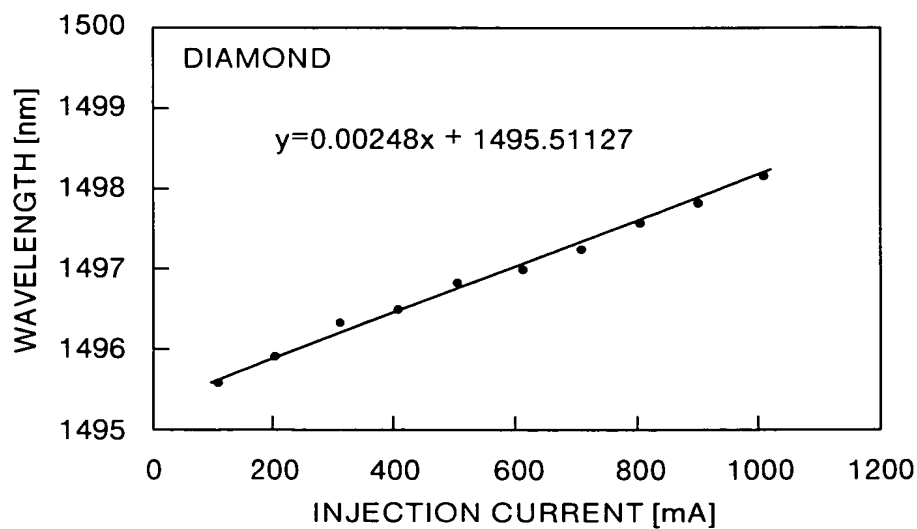




FIG.11

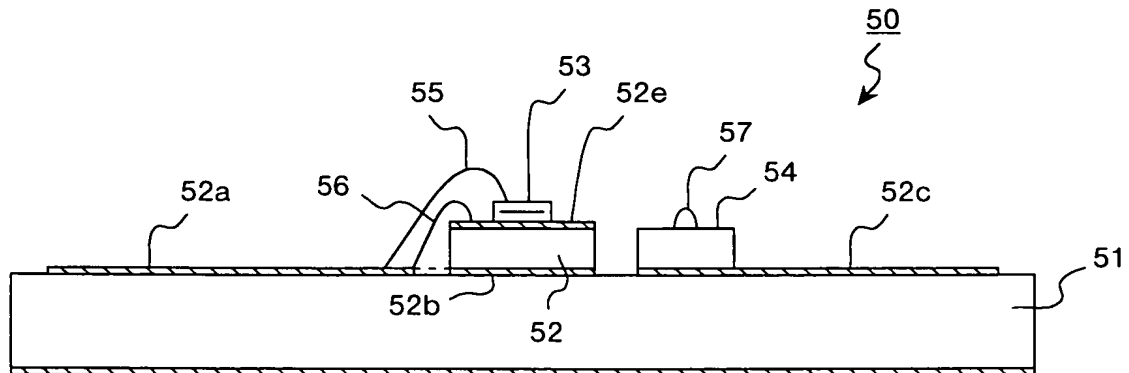


FIG.12A

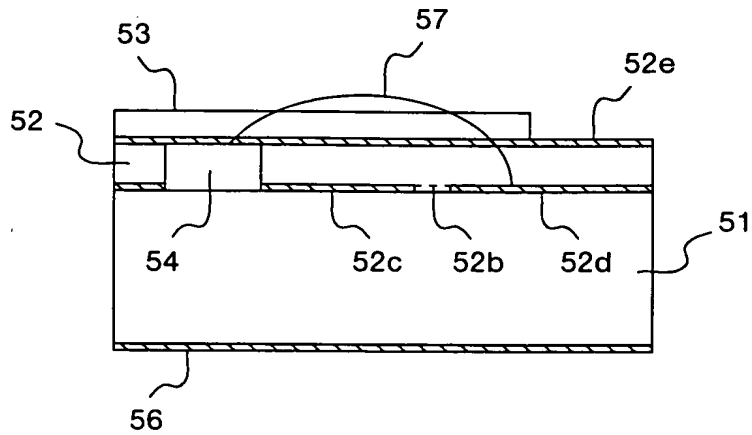
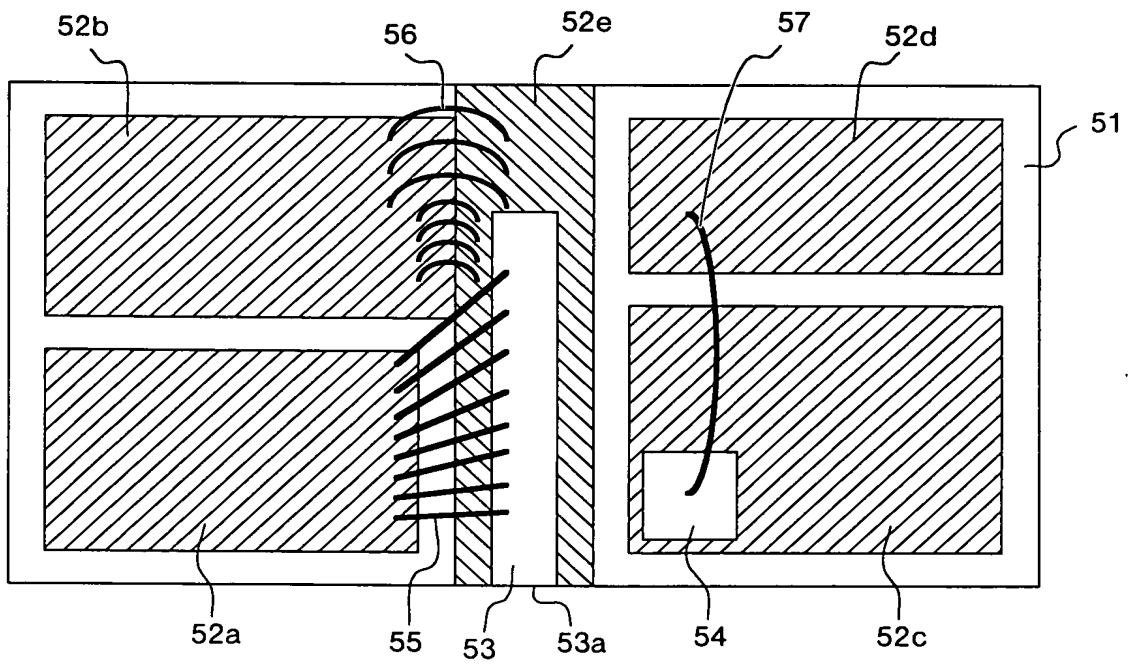
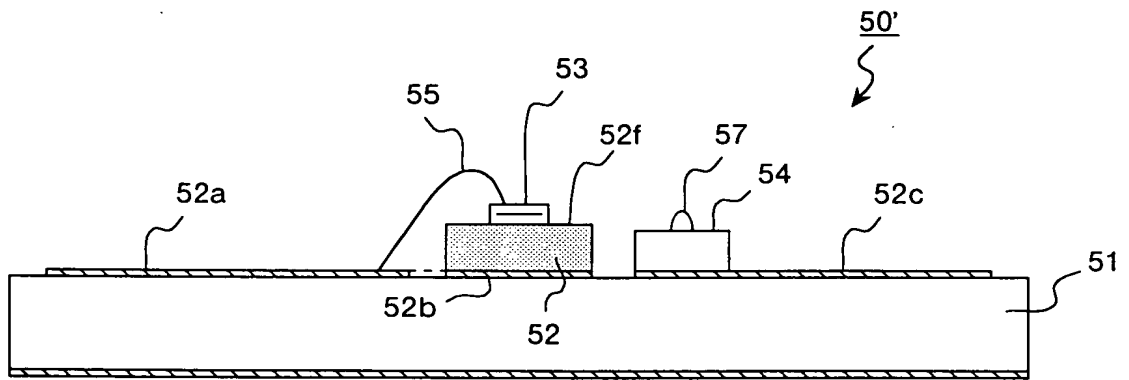


FIG.12B



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FIG.13



203000 216465.DOT

FIG.14A

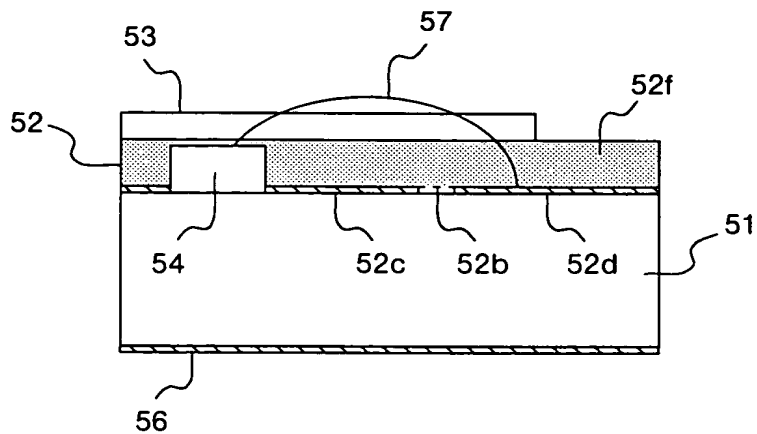
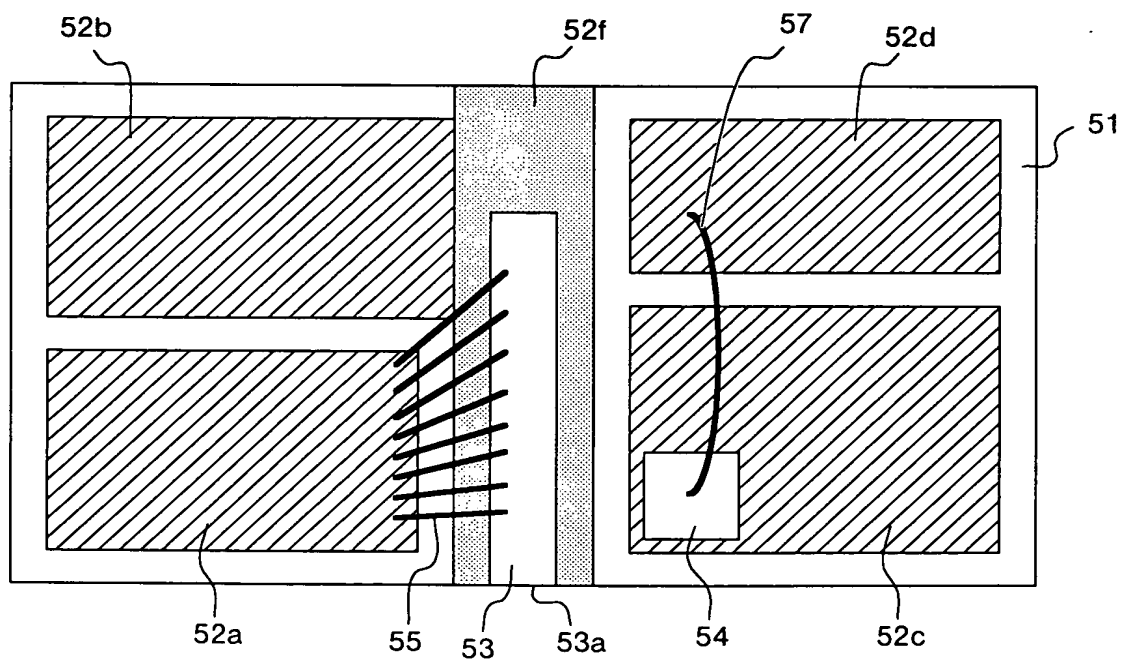
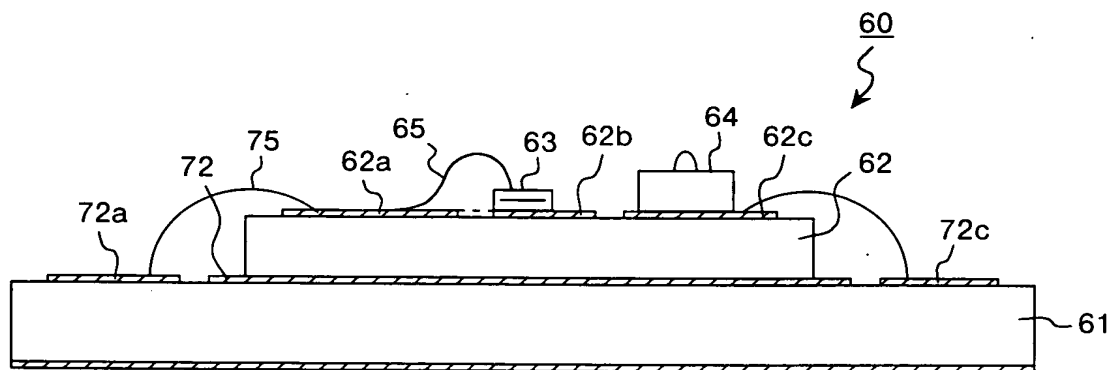


FIG.14B



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FIG.15



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FIG.16A

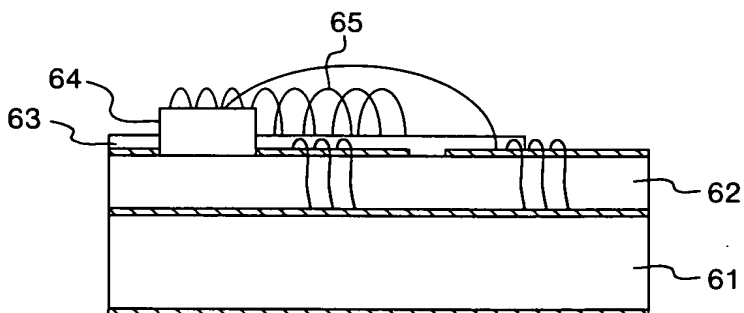
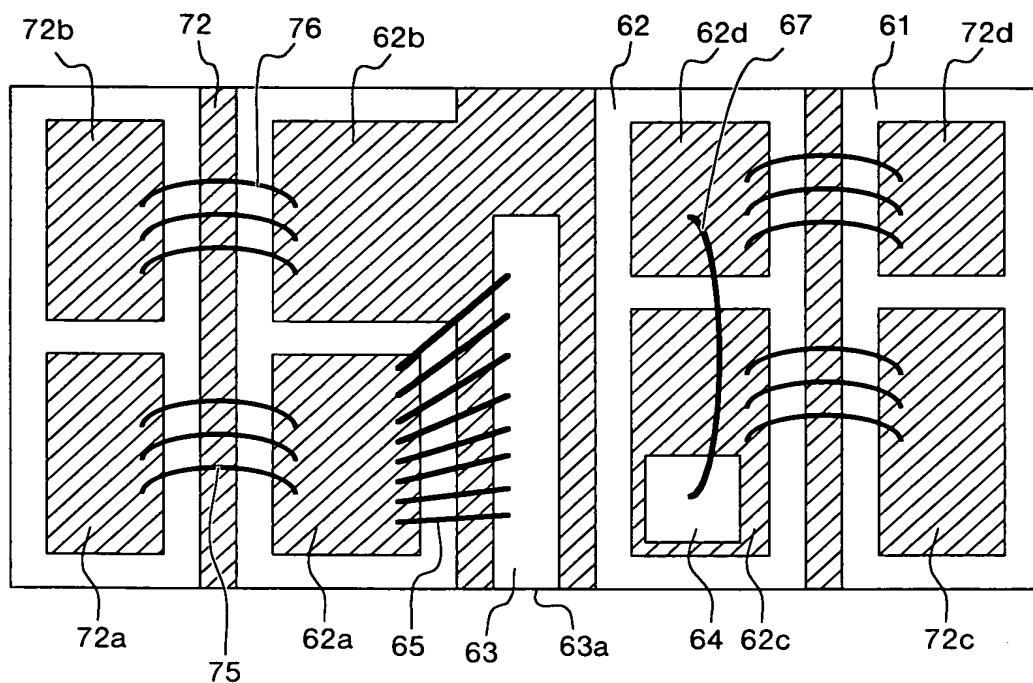
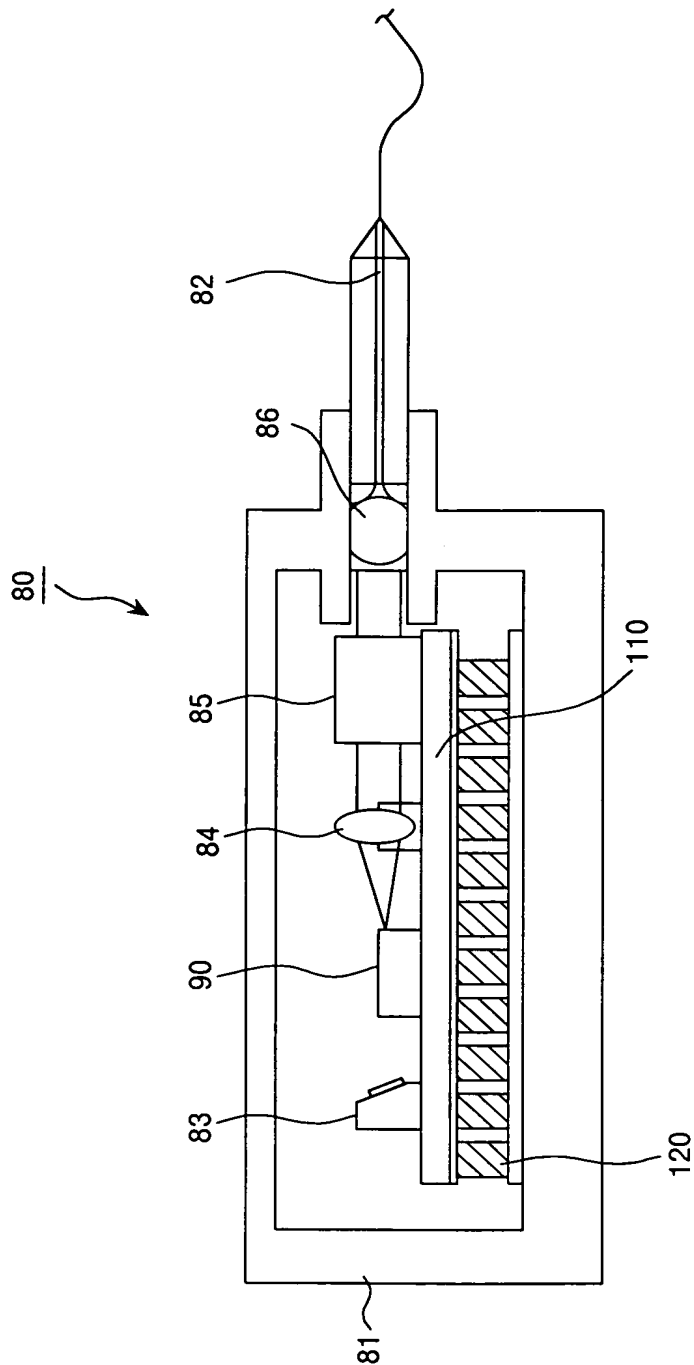


FIG.16B



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FIG.17



A cross-sectional view of a semiconductor device. The device consists of a substrate with a patterned layer 101, a layer 102, and a layer 104. A central structure 103 is connected to a pad 105 via a wire 102a. A large pad 106a is on the left, and a smaller pad 106b is on the right. A layer 104a is on the right side of the central structure.